

DIFFUSED-JUNCTION SILICON RECTIFIERS

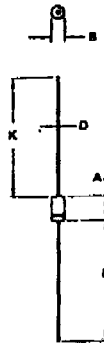
*absolute maximum ratings at specified ambient temperature

	1N2069	1N2070	1N2071	1N2069A	1N2070A	1N2071A	UNIT
$V_{RM}(=V_R)$	200	400	600	200	400	600	V
V_R	200	400	600	200	400	600	V
I_O	750						mA
I_{O10}	500						mA
$I_{FM(rep)}$	6						A
$I_{FM(surge)}$	22						A
$T_{A(lec)}$	-30 to 100			-35 to 100			°C
T_{stg}	-30 to 100			-35 to 100			°C
	Lead Temperature 1/2 Inch from Case for 5 Seconds (See Note 4)						°C

- NOTES 1. These values may be applied continuously under single-phase, 60-c/s, half-sine-wave operation with resistive load. Above 25°C derate I_O according to Figure 1.
2. These values apply for 60-c/s half sine waves when the device is operating at (or below) rated values of peak reverse voltage and average rectified forward current. Surge may be repeated after the device has returned to original thermal equilibrium.
3. Derate linearly to 4 A at 100°C.
4. It is recommended that a heat sink, such as long-nose pliers, be applied between the point of soldering and the rectifier body.

*indicates JEDEC registered data.

[†]The ambient temperature is measured at a point 2 inches below the device. Natural air cooling shall be used.



- NOTES:
1. POLARITY DENOTED BY CATHODE BAND.
 2. LEAD DIAMETER NOT CONTROLLED WITHIN "A" DIMENSION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.37	0.50	0.23	0.39
B	2.75	3.00	0.110	0.120
C	0.75	0.80	0.030	0.032
K	7.62	-	0.30	-

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

